

# 40 V, 0.5 A PNP low VCEsat (BISS) transistor Rev. 1 — 7 March 2012

Product data sheet

#### **Product profile** 1.

#### **1.1 General description**

PNP low V<sub>CEsat</sub> Breakthrough In Small Signal (BISS) transistor in a leadless ultra small SOT883B Surface-Mounted Device (SMD) plastic package.

NPN complement: PBSS2540MB.

#### 1.2 Features and benefits

- Leadless ultra small SMD plastic package
- Low package height of 0.37 mm
- Low collector-emitter saturation voltage V<sub>CEsat</sub>
- High collector current capability I<sub>C</sub> and I<sub>CM</sub>

#### **1.3 Applications**

- DC-to-DC conversion
- Supply line switching
- Battery charger

#### High efficiency due to less heat generation

- AEC-Q101 qualified
- Reduced Printed-Circuit Board (PCB) requirements
- LCD backlighting
- Driver in low supply voltage applications (e.g. lamps and LEDs)

#### 1.4 Quick reference data

Table 1.	Quick reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{CEO}$	collector-emitter voltage	open base	-	-	-40	V
I <sub>C</sub>	collector current		-	-	-500	mA
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms	-	-	-1	А
R <sub>CEsat</sub>	collector-emitter saturation resistance	$I_{C}$ = -500 mA; $I_{B}$ = -50 mA; pulsed; $t_{p} \le 300$ μs; δ ≤ 0.02 ; $T_{amb}$ = 25 °C	-	440	700	mΩ



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### 2. Pinning information

Table 2.	Pinning	j information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base		
2	E	emitter		3
3	С	collector	2	1
			Transparent top view	2
			SOT883B	sym013

### 3. Ordering information

Table 3. Ordering information						
Type number Package						
	Name	Description	Version			
PBSS3540MB	-	Leadless ultra small plastic package; 3 solder lands; body 1.0 x 0.6 x 0.37 mm	SOT883B			

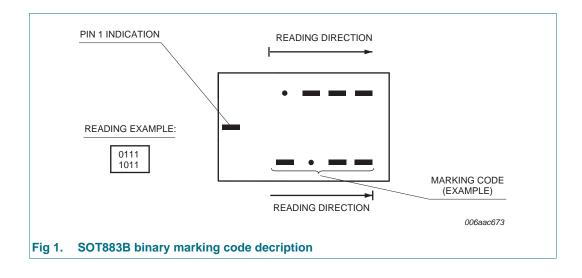
### 4. Marking

Table 4.	Marking	codes
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Type number	Marking code <sup>[1]</sup>
PBSS3540MB	0001 0100

[1] For SOT883B binary marking code description see Figure 1.

#### 4.1 Binary marking code description



40 V, 0.5 A PNP low VCEsat (BISS) transistor

### 5. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>CBO</sub>	collector-base voltage	open emitter		-	-40	V
V <sub>CEO</sub>	collector-emitter voltage	open base		-	-40	V
V <sub>EBO</sub>	emitter-base voltage	open collector		-	-6	V
I <sub>C</sub>	collector current			-	-500	mA
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms		-	-1	А
I <sub>BM</sub>	peak base current	single pulse; t <sub>p</sub> ≤ 1 ms		-	-100	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	<u>[1][2]</u>	-	250	mW
			[3][2]	-	590	mW
Tj	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Reflow soldering is the only recommended soldering method.

[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.

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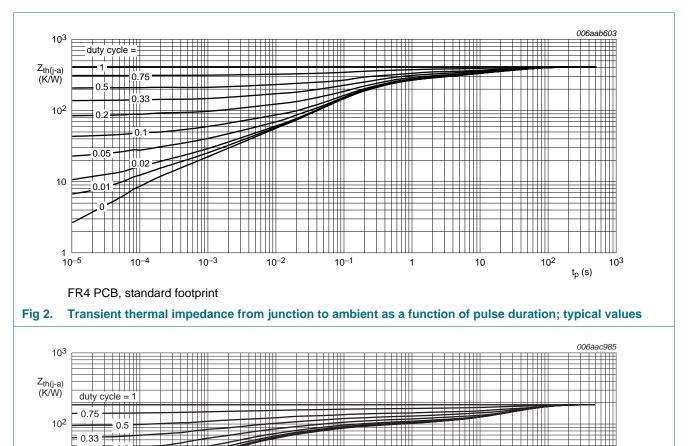
#### **Thermal characteristics** 6.

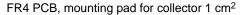
Table 6.	Thermal characteristics						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-a)</sub>	thermal resistance	in free air	[1][2]	-	-	500	K/W
	from junction to ambient		[3][2]	-	-	212	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Reflow soldering is the only recommented soldering method.

[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.





10<sup>-3</sup>

T

Transient thermal impedance from junction to ambient as a function of pulse duration; typical values Fig 3.

10-1

#

10-2

1

10

PBSS3540MB

0.33

0.1

0

1 – 10<sup>-5</sup>

10

++ 0.2

0.05

0.02 ++++

0.01

10-4

103

t<sub>p</sub> (s)

102

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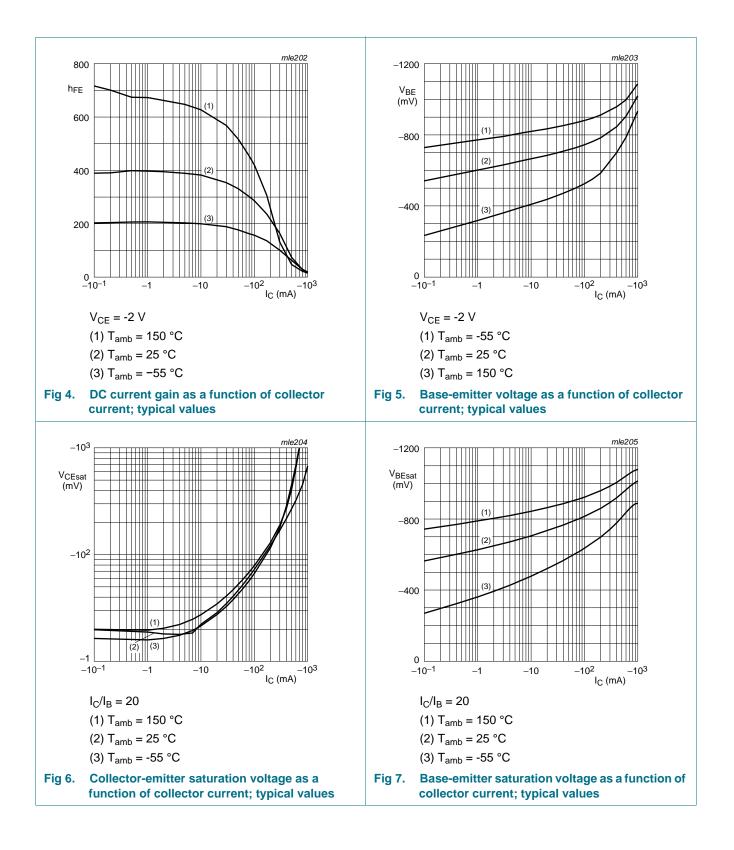
### 7. Characteristics

Table 7.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I <sub>CBO</sub>	collector-base cut-off	$V_{CB} = -30 \text{ V}; I_{E} = 0 \text{ A}; T_{amb} = 25 \text{ °C}$	-	-	-100	nA
	current	$V_{CB}$ = -30 V; I <sub>E</sub> = 0 A; T <sub>j</sub> = 150 °C	-	-	-50	μA
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; \text{ I}_{C} = 0 \text{ A}; \text{ T}_{amb} = 25 \text{ °C}$	-	-	-100	nA
h <sub>FE</sub>	DC current gain	$V_{CE}$ = -2 V; I <sub>C</sub> = -10 mA; T <sub>amb</sub> = 25 °C	200	-	-	
		$ \begin{array}{l} V_{CE} = -2 \ \text{V;} \ \text{I}_{C} = -100 \ \text{mA; pulsed;} \\ \text{t}_{p} \leq 300 \ \text{\mus;} \ \delta \leq 0.02 \ \text{;} \ \text{T}_{amb} = 25 \ ^{\circ}\text{C} \end{array} $	150	-	-	
		$      V_{CE} = -2 \text{ V}; \text{ I}_{C} = -500 \text{ mA}; \text{ pulsed};                                    $	40	-	-	
V <sub>CEsat</sub>	collector-emitter	$I_C$ = -10 mA; $I_B$ = -0.5 mA; $T_{amb}$ = 25 $^\circ C$	-	-	-50	mV
	saturation voltage	$I_C$ = -100 mA; $I_B$ = -5 mA; pulsed; $t_p \le 300$ μs; δ ≤ 0.02 ; $T_{amb}$ = 25 °C	-	-	-130	mV
		$I_C$ = -200 mA; $I_B$ = -10 mA; pulsed; $t_p \le 300$ μs; δ ≤ 0.02 ; $T_{amb}$ = 25 °C	-	-	-200	mV
		$\begin{split} I_C &= -500 \text{ mA; } I_B = -50 \text{ mA; pulsed;} \\ t_p &\leq 300  \mu\text{s; } \delta \leq 0.02 \text{ ; } T_{amb} = 25 ^\circ\text{C} \end{split}$	-	-	-350	mV
R <sub>CEsat</sub>	collector-emitter saturation resistance	$    I_C = -500 \text{ mA}; I_B = -50 \text{ mA}; \text{ pulsed};                                    $	-	440	700	mΩ
V <sub>BEsat</sub>	base-emitter saturation voltage	$    I_C = -500 \text{ mA}; I_B = -50 \text{ mA}; \text{ pulsed};                                    $	-	-	-1.2	V
V <sub>BEon</sub>	base-emitter turn-on voltage		-	-	-1.1	V
f <sub>T</sub>	transition frequency	$V_{CE}$ = -5 V; I <sub>C</sub> = -100 mA; f = 100 MHz; T <sub>amb</sub> = 25 °C	100	300	-	MHz
C <sub>c</sub>	collector capacitance	V <sub>CB</sub> = -10 V; I <sub>E</sub> = 0 A; i <sub>e</sub> = 0 A; f = 1 MHz; T <sub>amb</sub> = 25 °C	-	-	10	pF

#### **NXP Semiconductors**

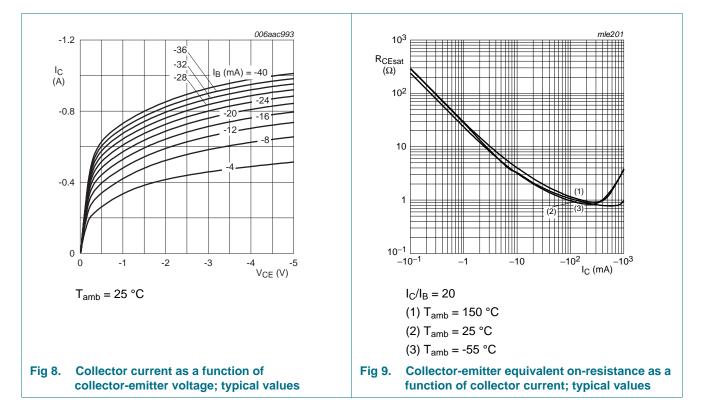
# PBSS3540MB

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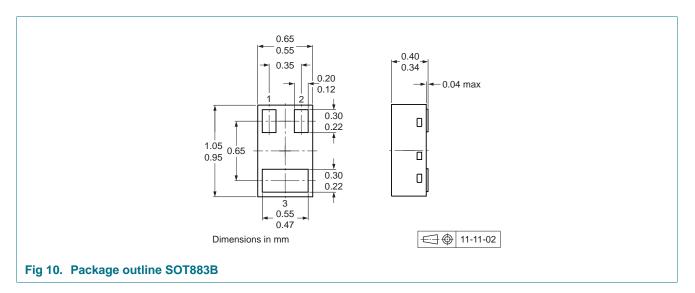
### 8. Test information

#### 8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

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### 9. Package outline



### 10. Soldering

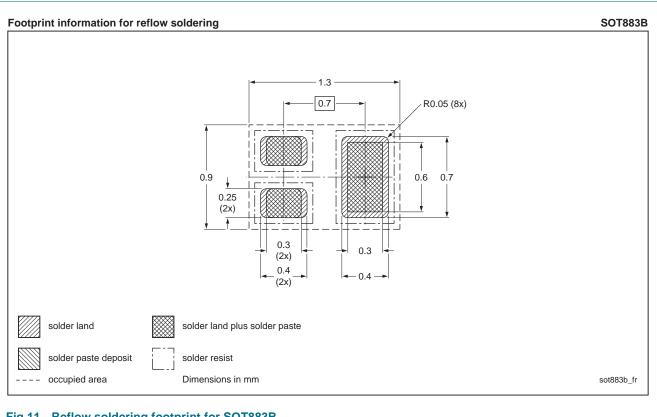


Fig 11. Reflow soldering footprint for SOT883B

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### **11. Revision history**

Table 8. Revis	Revision history							
Document ID	Release date	Data sheet status	Change notice	Supersedes				
PBSS3540MB v.1	20120307	Product data sheet	-	-				

40 V, 0.5 A PNP low VCEsat (BISS) transistor

### 12. Legal information

#### 12.1 Data sheet status

Document status[1] [2]	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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Date of release: 7 March 2012 Document identifier: PBSS3540MB